

Medium power transistor (–30V, –1A)

2SA2086S

●Features

- 1) High speed switching. (T_f : Typ. : 20ns at $I_c = -1A$)
- 2) Low saturation voltage, typically
(Typ. : –150mV at $I_c = -1.0A$, $I_B = -100mA$)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SC5874S

●Applications

Small signal low frequency amplifier
High speed switching

●Structure

PNP Silicon epitaxial planar transistor

●Packaging specifications

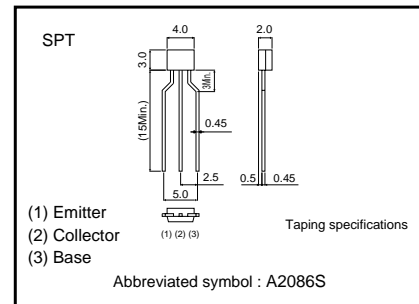
Type	Package	Taping
	Code	TP
	Basic ordering unit (pieces)	5000
2SA2086S		○

●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	–30	V	
Collector-emitter voltage	V_{CEO}	–30	V	
Emitter-base voltage	V_{EBO}	–6	V	
Collector current	DC	I_c	–1	A
	Pulsed	I_{cP}	–2	A *
Power dissipation	P_c	300	mW	
Junction temperature	T_j	150	$^\circ\text{C}$	
Range of storage temperature	T_{stg}	–55 to 150	$^\circ\text{C}$	

* $P_w=10ms$

●External dimensions (Unit : mm)



Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Collector-emitter breakdown voltage	BV _{CEO}	-30	-	-	V	I _C = -1mA
Collector-base breakdown voltage	BV _{CBO}	-30	-	-	V	I _C = -100μA
Emitter-base breakdown voltage	BV _{EBO}	-6	-	-	V	I _E = -100μA
Collector cut-off current	I _{CBO}	-	-	-1.0	μA	V _{CB} = -20V
Emitter cut-off current	I _{EBO}	-	-	-1.0	μA	V _{EB} = -4V
Collector-emitter saturation voltage	V _{CE(sat)}	120	-150	-300	mV	I _C = -1.0A I _B = -100mA
DC current gain	h _{FE}	-	-	390	-	V _{CE} = -2V I _C = -100mA
Transition frequency	f _T	-	350	-	MHz	V _{CE} = -10V I _E =100mA f=10MHz
Corrector output capacitance	C _{ob}	-	10	-	pF	V _{CB} = -10V I _E =0mA f=1MHz
Turn-on time	T _{on}	-	30	-	ns	I _C = -1A I _{B1} = -100mA
Storage time	T _{stg}	-	100	-	ns	I _{B2} =100mA
Fall time	T _f	-	20	-	ns	V _{CC} = -25V

*Non repetitive pulse

●h_{FE} RANK

Q	R
120-270	180-390

●Electrical characteristic curves

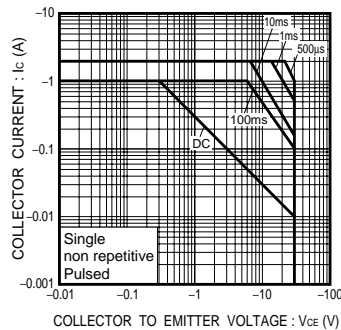


Fig.1 Safe Operating Area

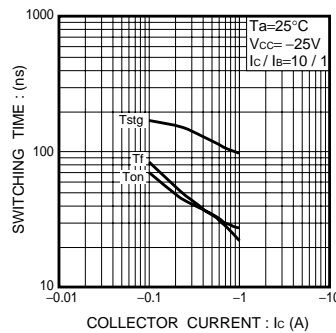


Fig.2 Switching Time

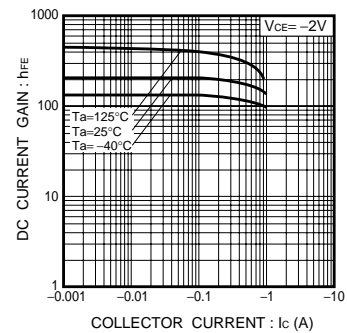


Fig.3 DC Current Gain vs. Collector Current (I)

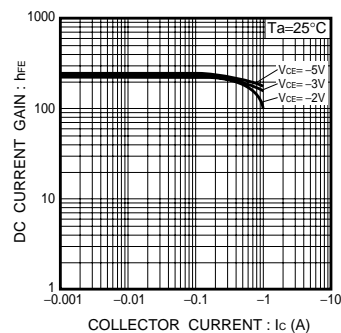


Fig.4 DC Current Gain vs. Collector Current (II)

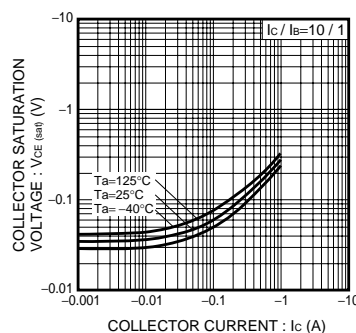


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

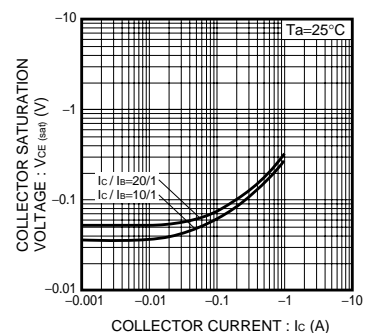


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

Transistors

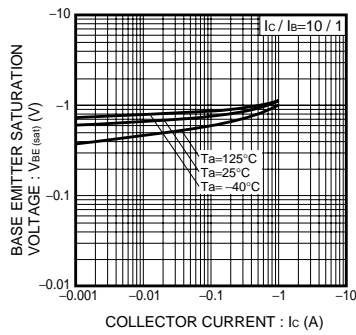


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

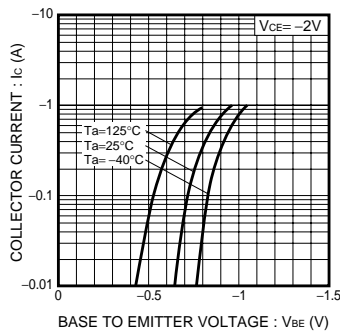


Fig.8 Grounded Emitter Propagation Characteristics

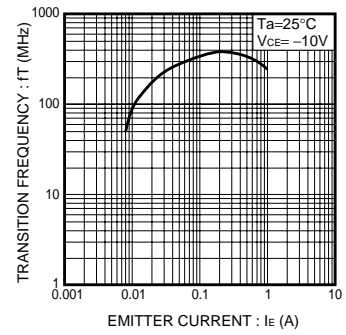


Fig.9 Transition Frequency

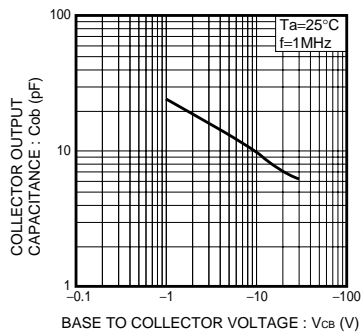
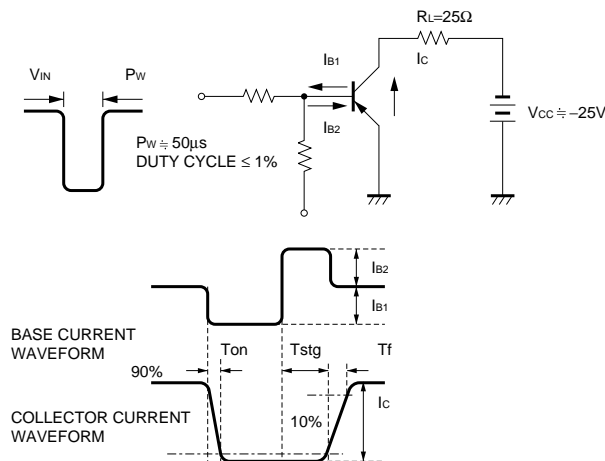


Fig.10 Collector Output Capacitance

●Switching characteristics measurement circuits



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